

ABSTRACT OF THE DISCLOSURE

A nonvolatile semiconductor memory device includes a memory cell transistor which is configured to store two bits inclusive of a first
5 bit and a second bit at respective ends of an electric charge capturing film, a comparator which checks a data status by reading data of the first bit, and a potential switching circuit which changes
10 potential conditions for writing of the second bit in response to whether the data status is 0 or 1.